

Abstracts

A 30 GHz - 100 mW GaAs FET

O. Ishihara, Y. Kadowaki, M. Nakatani, A. Nara and K. Shirahata. "A 30 GHz - 100 mW GaAs FET." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 325-327.

Power output of 100 mW and linear power gain of 5 dB have been realized at 30 GHz for the GaAs FET fabricated by optimizing physical parameters of the channel for high power end.

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